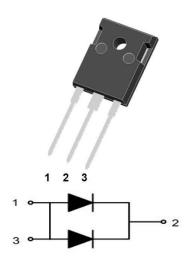


Silicon Carbide Schottky Diode

V_{RRM}	1200V	
I _{F (135°C)}	52A	
Qc	216nC	



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero reverse recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

• Package: TO-247AB

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_C=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112040NCQG2
Reverse voltage (repetitive peak) @ T _j =25°C	V_{RRM}	V	1200
Reverse voltage (Surge Peak) @ T _j =25°C	V _{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	1200
Continuous forward current @ T_c =25°C T_c =135°C T_c =150°C	l _F	А	108 52 40
Non-repetitive peak forward surge current @ T _c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	300
Non-repetitive peak forward surge current @ T _c =25°C, tp=10us,square wave	I _{FSM}	А	2400
Power Dissipation@ T _c =25°C T _c =110°C	Ртот	W	468 203
i²t Value@ Tc=25°C ,tp=10ms	∫ i²dt	A ² S	450
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175



■Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.	
Forward voltage drop	VF	V	I _F =40A, T _j =25°C	1.41	1.58	
			I _F =40A, T _j =175°C	2.02	2.2	
Poverse leakage current	everse leakage current I _R µA	V _R =1200V, T _j =25°C	2	38		
Neverse leakage current		μΑ	V _R =1200V, T _j =175°C	19	200	
Total capacitive charge	Qc	nC	$V_R=800V$, $T_j=25^{\circ}C$, $QC=\int_0^{VR}C(V)dV$	216		
			V _R =0V, f=1MHZ	2900		
Total capacitance	C pF	С	pF	V _R =400V, f=1MHZ	204	
			V _R =800V, f=1MHZ	156		
Capacitance Stored Energy	Ec	μJ	V _R =800V	55		

■Thermal Characteristics $(T_a=25$ $^{\circ}$ C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Тур	Max
Thermal resistance	R _{eJ-C}	°C W	0.30	0.32

■Characteristics (Typical)

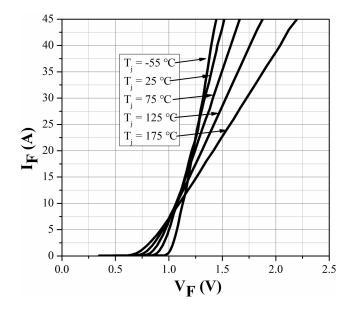


Figure 1. Forward Characteristics

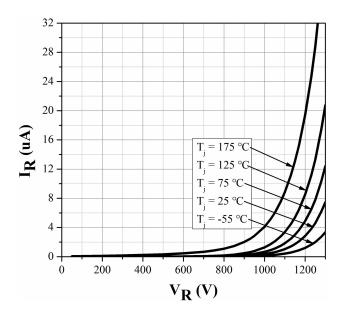
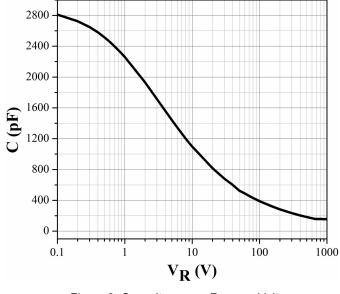


Figure 2. Reverse Characteristic





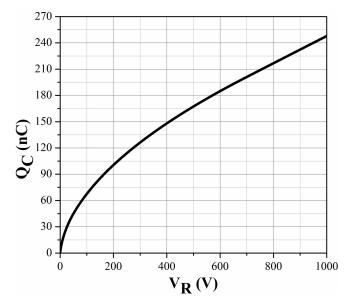
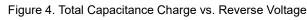
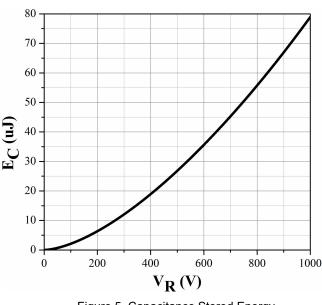
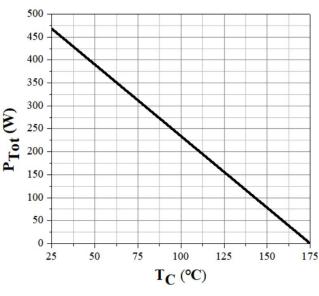
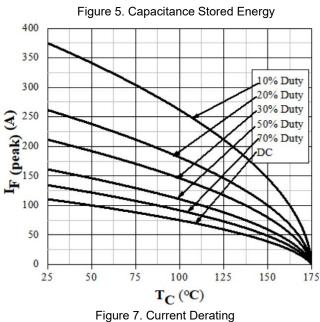


Figure 3. Capacitance vs. Reverse Voltage









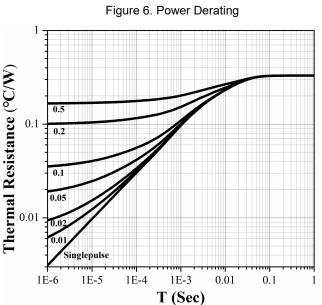
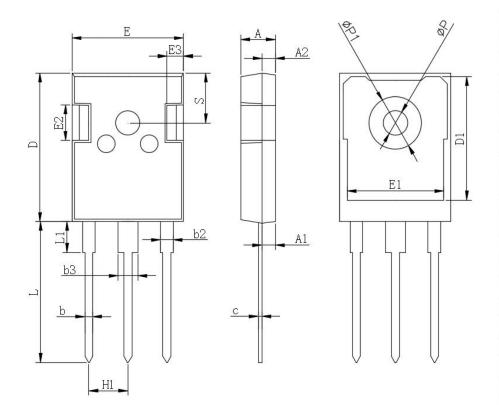


Figure 8. Transient Thermal Impedance



■Outline Dimensions



TO-247AB				
Dim	Min	Max		
Α	4.8	5.2		
A1	2.21	2.61		
A2	1.85	2.15		
b	1	1.4		
b2	1.91	2.21		
С	0.5	0.7		
D	20.7	21.3		
D1	16.25	16.85		
E	15.5	16.1		
E1	13	13.6		
E2	4.8	5.2		
E3	2.3	2.7		
L	19.62	20.22		
L1		4.3		
ФР	3.4	3.8		
ΦΡ1		7.3		
S	6.15TYP			
H1	5.44TYP			





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